

What is claimed is:

1. A method of preventing generation of particles in a chamber, the method comprising:

mounting a substrate within a chamber of a gas-exposure equipment;
decreasing a pressure within the chamber;
injecting a surface treatment gas into the chamber; and
drawing out the surface treatment gas from the chamber while
injecting a nitrogen gas into the chamber.

2. The method as claimed in claim 1, wherein drawing out the surface treatment gas also causes the pressure in the chamber to become equal to an atmospheric pressure.

3. The method as claimed in claim 1, wherein the drawing out of the surface treatment gas also causes the pressure in the chamber to become higher than an atmospheric pressure.

4. The method as claimed in claim 1, wherein the gas includes HMDS gas.

5. The method as claimed in claim 1, wherein the step of injecting the surface treatment gas converts the surface of the substrate into an organic material.

1 6. The method as claimed in claim 1, wherein the chamber includes
2 evacuation lines and ejection lines.
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1 7. The method as claimed in claim 6, wherein the nitrogen gas is
2 applied to the chamber through the ejection lines.
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1 8. The method as claimed in claim 6, wherein the step of evacuating
2 includes evacuating the gas through the evacuation lines.
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1 9. The method as claimed in claim 1, wherein the substrate is a thin
2 film transistor substrate.
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1 10. The method as claimed in claim 9, wherein the thin film transistor
2 substrate includes at least one of a gate electrode, a source electrode, a
3 drain electrode, and a pixel electrode.
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1 11. The method as claimed in claim 1, wherein the substrate includes
2 color filter substrate.
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1 12. The method as claimed in claim 11, wherein the color filter
2 substrate includes at least one of a color filter and a black matrix.
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1 13. A method to prevent generation of contaminating particles in a
2 chamber, the method comprising:
3 evacuating an ordinary gas within said chamber;

4 injecting a treatment gas into said chamber to treat a surface of a
5 substrate; and

6 withdrawing said treatment gas from said chamber while injecting a
7 moisture displacing gas into said chamber.

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1 14. The method of claim 13, wherein said moisture displacing gas is
2 nitrogen.

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1 15. The method of claim 13, wherein said treatment gas is HMDS.

2
1 16. The method of claim 13, wherein a pressure within said chamber
2 rises to be equal to or above an atmospheric pressure as said moisture
3 displacing gas is injected into said chamber.